

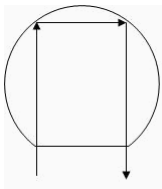
Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	150.00 +/- 0.20 mm	
	2.0 Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0 Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0 Secondary Flat Orientation	none	
	5.0 Overall Thickness	400.00 +/- 10.00 µm	ADE, 100%
	6.0 Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0 Bow	<40.00µm	ADE to ASTM F534, 20%
	8.0 Warp	<40.00µm	ADE to ASTM F657, 20%
	9.0 Edge Chips	None	Bright Light, 100% (note 2)
	10.0 Edge Exclusion	5mm	
	11.0 Frontsurface condition	Polished.	
	12.0 Lasermarking	Frontside. TE specific lasermark as per TE specification: WP-LS-WAFER-003 Revision 02a. SECTION 7.	Guaranteed by process
HandleSilicon	13.0 Frontside final oxide thickness	15,000.00 +/- 750.00 A	Nanospec centre point, 4%
	14.0 Back side Oxide Thickness	15,000.00 +/- 750.00 A	Nanospec centre point, 4%
	15.0 Handle Silicon Raw Material	Prime Silicon	
	16.0 Handle Growth Method	CZ	Wafer Vendor
	17.0 Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	18.0 Handle Thickness	400.00 +/- 10.00 µm	ADE, 100%
	19.0 Handle Doping Type	N	Wafer Vendor
	20.0 Handle Dopant	Phosphorous	Wafer Vendor
	21.0 Handle Resistivity	1 ~ 10 Ohmcm	Wafer Vendor
	22.0 Handle Oxygen Concentration	9 ~ 13.22 ppma. Accepted by customer.	Wafer vendor
	23.0 Backside Finish	Lapped / Etched with oxide.	Guaranteed by process
	24.0 Surface Haze	none	Bright Light, 100% (note 2)
	25.0 Total LPD Count	Front side <30 >0.3µm	Tencor particle counter
	26.0 Total scratch length	<= 1.0 cm	Bright Light, 100% (note2)
	27.0 Handle Silicon Dislocation Etch Pit Density	<100 / cm2	Preferential etching (Wright) where necessary

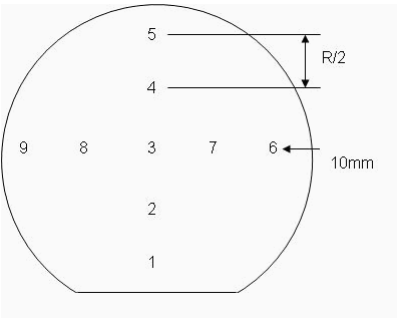
Part Number	Customer
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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information